TECHNICAL DATA DATA SHEET 1019, REV. B

SILICON SCHOTTKY RECTIFIER DIE Very Low Forward Voltage Drop (150 °C T_J Operation)

Applications:

• Switching Power Supply • Converters • Free-Wheeling Diodes • Polarity Protection Diode

Features:

- Soft Reverse Recovery at Low and High Temperature
- Very Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics
- Electrically / Mechanically Stable during and after Packaging

Maximum Ratings⁽¹⁾:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	60	V
Max. Average Forward Current	I _{F(AV)}	50% duty cycle, rectangular wave form	1	Α
Max. Peak One Cycle Non- Repetitive Surge Current	I _{FSM}	8.3 ms, half Sine wave	20	А
Non-Repetitive Avalanche Energy	E _{AS}	$T_J = 25 ^{\circ}\text{C}, \ I_{AS} = 0.74 A, \\ L = 18 \text{mH}$	5.0	mJ
Repetitive Avalanche Current	I _{AR}	I_{AS} decay linearly to 0 in 1 μ s f limited by T_J max V_A =1.5 V_R	0.74	А
Max. Junction Temperature	T_J	-	-65 to +150	°C
Max. Storage Temperature	T _{stg}	-	-65 to +150	°C

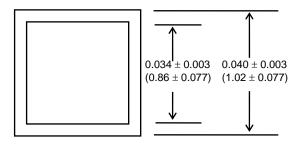
Electrical Characteristics(1):

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	V_{F1}	@ 1A, Pulse, T _J = 25 °C	0.60	V
	V_{F2}	@ 1A, Pulse, T _J = 125 °C	0.55	V
Max. Reverse Current	I _{R1}	@V _R = 60V, Pulse,	100	μА
		T _J = 25 °C		
	I_{R2}	$@V_R = 60V$, Pulse,	9.0	mA
		T _J = 125 °C		
Max. Junction Capacitance	C_T	$@V_R = 5V, T_C = 25 ^{\circ}C$	53	pF
		$f_{SIG} = 1MHz,$		
		$V_{SIG} = 50 \text{mV} \text{ (p-p)}$		

(1) in SHD package

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Mechanical Dimensions: In Inches / mm



<u></u> → H

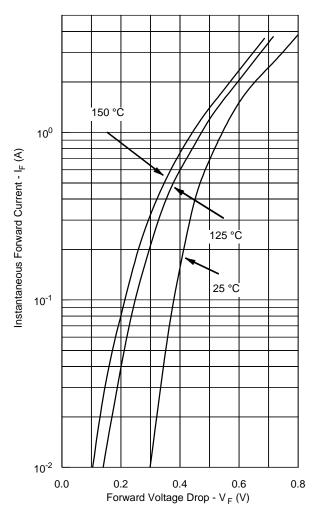
Bottom side metalization Ag - 30 kÅ minimum.

Top side metalization Al - 25 kÅ minimum or Ag - 30 kÅ minimum.

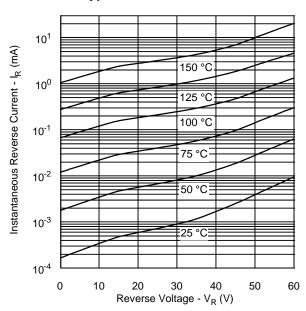
Bottom side is cathode, top side is anode.

Dimension H = 0.0105 ± 0.001 (0.27 \pm 0.026) for Al top; Dimension H = 0.0155 ± 0.001 (0.39 \pm 0.026) for Ag top.

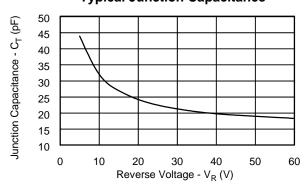
Typical Forward Characteristics



Typical Reverse Characteristics



Typical Junction Capacitance



SENSITRON

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